

## isc P-Channel MOSFET Transistor

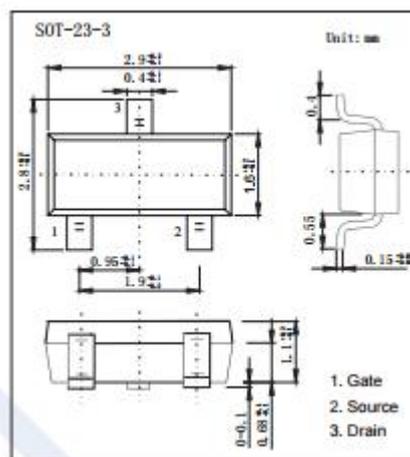
IRLML6402

## DESCRIPTION

- Ultra low on-resistance
- P-Channel MOSFET
- SOT-23 Footprint
- Available in tape and reel
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER  | VALUE    | UNIT             |
|-----------|--|----------|------------------|
| $V_{DSS}$ | Drain-Source Voltage ( $V_{GS}=0$ )              | -20      | V                |
| $V_{GS}$  | Gate-Source Voltage                              | $\pm 12$ | V                |
| $I_D$     | Drain Current-continuous@ $T_C=37^\circ\text{C}$ | -3.7     | A                |
| $I_{DM}$  | Drain Current Pulse                              | -30      | A                |
| $P_{tot}$ | Total Dissipation@ $T_A=25^\circ\text{C}$        | 1.3      | W                |
|           | Total Dissipation@ $T_A=75^\circ\text{C}$        | 0.8      | W                |
| $T_j$     | Max. Operating Junction Temperature              | -55~150  | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                        | -55~150  | $^\circ\text{C}$ |

## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                               | MAX | UNIT                      |
|---------------|---|-----|---------------------------|
| $R_{th\ j-a}$ | Thermal Resistance, Junction to Ambient | 100 | $^\circ\text{C}/\text{W}$ |

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## IRLML6402

• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)

| SYMBOL               | PARAMETER                        | CONDITIONS  | MIN  | MAX   | UNIT |
|----------------------|----------------------------------|---|------|-------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage   | V <sub>GS</sub> = 0; I <sub>D</sub> = -0.25mA                     | -20  |       | V    |
| V <sub>GS(TH)</sub>  | Gate Threshold Voltage           | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = -0.25mA      | -0.4 | -0.95 | V    |
| R <sub>DS(ON)</sub>  | Drain-Source On-stage Resistance | V <sub>GS</sub> = -4.5V; I <sub>D</sub> = -3.7A                   |      | 0.065 | Ω    |
|                      |                                  | V <sub>GS</sub> = -2.5V; I <sub>D</sub> = -3.1A                   |      | 0.135 | Ω    |
| I <sub>GSS</sub>     | Gate Source Leakage Current      | V <sub>GS</sub> = ±12V; V <sub>DS</sub> = 0                       |      | ±100  | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current  | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0                       |      | -1    | uA   |
|                      |                                  | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0, T <sub>J</sub> =70°C |      | -25   | uA   |
| V <sub>SD</sub>      | Diode Forward Voltage            | I <sub>F</sub> =-2 A; V <sub>GS</sub> = 0, T <sub>J</sub> =25°C   |      | -1.2  | V    |

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